

MMBT3906

SMALL SIGNAL PNP TRANSISTOR

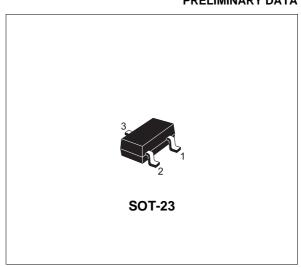
PRELIMINARY DATA

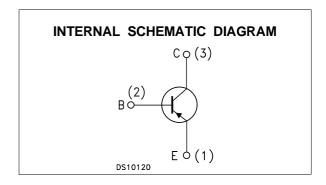
Туре	Marking	
MMBT3906	36	

- SILICON EPITAXIAL PLANAR PNP TRANSISTOR
- MINIATURE SOT-23 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE NPN COMPLEMENTARY TYPE IS MMBT3904

APPLICATIONS

- WELL SUITABLE FOR PORTABLE EQUIPMENT
- SMALL LOAD SWITCH TRANSISTOR WITH HIGH GAIN AND LOW SATURATION VOLTAGE





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage (I _E = 0)	-60	V
V_{CEO}	Collector-Emitter Voltage (I _B = 0)	-40	V
V_{EBO}	Emitter-Base Voltage (I _C = 0)	-6	V
Ic	Collector Current	-200	mA
P _{tot}	Total Dissipation at T _C = 25 °C	350	mW
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

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THERMAL DATA

R _{thj-amb} • T	Thermal Resistance Junction-Ambient	Max	357.1	°C/W	
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Device mounted on a PCB area of 1 cm²

ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

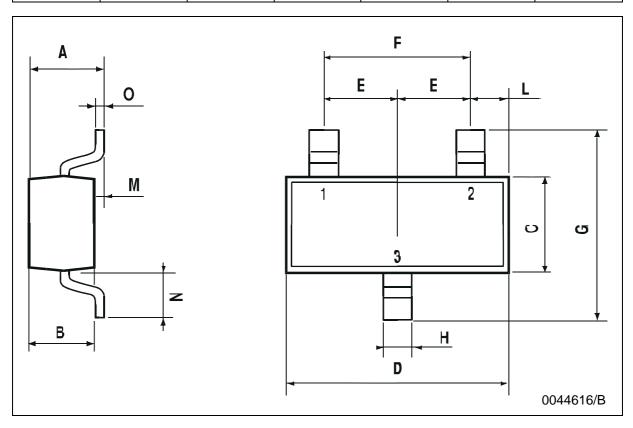
$\begin{array}{ c c c c c }\hline I_{CEX} & Collector Cut-off \\ Current (V_{BE}=3 \ V) & V_{CE}=-30 \ V \\ \hline \\ I_{BEX} & Collector Cut-off \\ Current (V_{BE}=3 \ V) & V_{CE}=-30 \ V \\ \hline \\ V_{(BR)CEO^*} & Collector-Emitter \\ Breakdown Voltage \\ (I_B=0) & I_C=-10 \ \mu A & -60 \\ \hline \\ V_{(BR)CBO} & Collector-Base \\ Breakdown Voltage \\ (I_E=0) & I_E=-10 \ \mu A & -6 \\ \hline \\ V_{(BR)EBO} & Emitter-Base \\ Breakdown Voltage \\ (I_C=0) & I_C=-10 \ mA & I_B=-1 \ mA \\ \hline \\ V_{CE(sat)^*} & Collector-Emitter & I_C=-10 \ mA & I_B=-1 \ mA \\ \hline \end{array}$	-50	nA nA V V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	-50	V
$\begin{array}{c} \text{Breakdown Voltage} \\ \text{(IB = 0)} \\ \\ \text{V}_{\text{(BR)CBO}} \\ \text{Collector-Base} \\ \text{Breakdown Voltage} \\ \text{(IE = 0)} \\ \\ \text{V}_{\text{(BR)EBO}} \\ \\ \text{Emitter-Base} \\ \text{Breakdown Voltage} \\ \text{(IC = 0)} \\ \end{array} \begin{array}{c} \text{IC = -10 } \mu\text{A} \\ \text{IE = -10 } \mu\text{A} \\ \text{-6} \\ \\ \text{Breakdown Voltage} \\ \text{(IC = 0)} \\ \end{array}$		V
Breakdown Voltage ($I_E=0$) $V_{(BR)EBO}$ Emitter-Base Breakdown Voltage ($I_C=0$) $I_E=-10~\mu A$ -6		
Breakdown Voltage (Ic = 0)		V
Variable Collector Emitter		
$V_{CE(sat)}^*$ Collector-Emitter $I_C = -10 \text{ mA}$ $I_B = -1 \text{ mA}$ $I_B = -5 \text{ mA}$	-0.25 -0.4	V V
$V_{BE(sat)}*$ Base-Emitter $I_{C}=-10$ mA $I_{B}=-1$ mA $I_{C}=-50$ mA $I_{B}=-5$ mA $I_{C}=-0.65$	-0.85 -0.95	V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	300	
f_T Transition Frequency $I_C = -10 \text{mA} \ V_{CE} = -20 \ \text{V} \ f = 100 \text{MHz}$ 250		MHz
NF Noise Figure $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		dB
C_{CBO} Collector-Base $I_E = 0$ $V_{CB} = -5$ V $f = 100$ KHz 6		pF
C_{EBO} Emitter-Base $I_C = 0$ $V_{EB} = -0.5 \text{ V}$ $f = 100 \text{ KHz}$ 25 Capacitance		pF
t_d Delay Time $I_C = -10 \text{ mA}$ $I_B = -1 \text{ mA}$	35	ns
t_r Rise Time $V_{CC} = -3V$	35	ns
t_s Storage Time $I_C = -10 \text{ mA}$ $I_{B1} = -I_{B2} = -1 \text{ mA}$	225	ns
t _f Fall Time Vcc = -3V	72	ns

^{*} Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %

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SOT-23 MECHANICAL DATA

DIM.	mm		mils			
Diiii.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	0.85		1.1	33.4		43.3
В	0.65		0.95	25.6		37.4
С	1.20		1.4	47.2		55.1
D	2.80		3	110.2		118
E	0.95		1.05	37.4		41.3
F	1.9		2.05	74.8		80.7
G	2.1		2.5	82.6		98.4
Н	0.38		0.48	14.9		18.8
L	0.3		0.6	11.8		23.6
М	0		0.1	0		3.9
N	0.3		0.65	11.8		25.6
0	0.09		0.17	3.5		6.7



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